Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1	10/670928	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/06/13 09:37
L2	940	strained near3 silicon	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/06/13 10:38
L3	6	strained near3 silicon adj nitride	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/06/13 09:38
L4	1248	("SOI" semiconductor adj on adj insulator) with (silicon adj germanium 'sige')	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/06/13 10:40
L5	359	4 and (crystal$5) with (silicon adj germanium 'sige')	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/06/13 10:41
L6	44	5 and (nitridation nitrify nitrification silicide silicidation oxynitridation) with (silicon adj germanium 'sige')	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/06/13 10:44
L7	118	5 and (implant$4 nitridation nitrify nitrification silicide silicidation oxynitridation) with (silicon adj germanium 'sige')	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/06/13 13:52
L8	147	5 and (implant$4 nitridation nitrify nitrification silicide silicidation oxynitridation oxidation) with (silicon adj germanium 'sige')	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/06/13 13:52
L9	1	8 and (stained) with (silicon adj germanium 'sige')	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/06/13 13:53

L10	99	8 and (strained) with (silicon adj germanium 'sige')	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/06/13 14:58
L11	19	10 and (nitride) with (silicon adj germanium 'sige')	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/06/13 15:18
L12	0	10 and (oxynitride) with (silicon adj germanium 'sige')	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/06/13 15:18

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S29	6	"6524935"	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/04/21 08:40
S30	862	("SiGe" 'sige' silicon near3 geranium) with (strained relaxed)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/04/21 09:04
S31	632	S30 and (implant$3 nitridation nitrify nitrification inject$3 silicide silicidation)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/04/21 09:02
S32	632	S30 and (implant$3 nitridation nitrify nitrification inject$3 silicide silicidation oxynitridation)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/04/21 09:03
S33	175	S32 and ("SiGe" 'sige' silicon near3 geranium) with (crystalline ((mono single) near3 (crystal crystalline)))	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/04/21 09:07
S34	166	S33 and ("SiGe" 'sige' silicon near3 geranium) with ('soi' insulat$3 substrate)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/04/21 09:08
S35	166	S34 and (nitride silicon oxynitride nitrogen germanium metal metali$4 heat$3 anneal$3 oxide)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/04/21 10:16
S37	1	S35 and vacan$3	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/04/21 09:12
S38	95	S35 and $4nitrid$7	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/04/21 18:08
S39	10	"6455398"	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/04/21 18:08
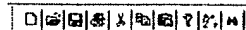
BRS:
⊖ Pending
⊞ Active
—⇘ L1: (1) 10/670928
—⇘ L3: (6) strained near3 silicon adj nitride
—⇘ L2: (940) strained near3 silicon
—⇘ L4: (1248) ("SOI" semiconductor adj on adj insulator) with (silicon adj germanium 'sige')
—⇘ L5: (359) 4 and (crystal$5) with (silicon adj germanium 'sige')
—⇘ L6: (44) 5 and (nitridation nitrify nitrification silicide silicidation oxynitridation) with (sil...
—⇘ L7: (118) 5 and (implant$4 nitridation nitrify nitrification silicide silicidation oxynitridation...
—⇘ L8: (147) 5 and (implant$4 nitridation nitrify nitrification silicide silicidation oxynitridation...
—⇘ L9: (1) 8 and (stained) with (silicon adj germanium 'sige')
—⇘ L10: (99) 8 and (strained) with (silicon adj germanium 'sige')
—⇘ L11: (19) 10 and (nitride) with (silicon adj germanium 'sige')
—⇘ L12: (0) 10 and (oxynitride) with (silicon adj germanium 'sige')
—⇘ L13: (125) (oxynitride) with (silicon adj germanium 'sige')
⊞ Failed

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DBs | US-PGPUB; USPAT; EPO; JPO   ☑ Plurals
Default operator: OR ▾   ☑ Highlight all hit terms initially

(oxynitride) with (silicon adj germanium 'sige')

BRS form | IS&R form | Image | Text | HTML

	U	1	Document I	Issue Dat	Page	Title	Current O	Current X	Retrieval	Inventor	S	C	P	2	3	
1	☐	☐	US 2005012	2005060	27	Semiconductor device an	438/197			Kanemoto, Kei	☑	☐	☐	☐	☐	☐
2	☐	☐	US 2005011	2005060	13	Dielectrics with improved	438/786			Chou, Anthony I. et	☑	☐	☐	☐	☐	☐
3	☐	☐	US 2005008	2005042	8	Multi-layer dielectric con	438/763			Adetutu, Olubunmi	☑	☐	☐	☐	☐	☐
4	☐	☐	US 2005008	2005042	18	Surface engineering of na	427/212	427/372.2		Yadav, Tapesh et al.	☑	☐	☐	☐	☐	☐
5	☐	☐	US 2005006	2005033	12	Memory cell with nanocr	257/390	257/321;		Gutsche, Martin et	☑	☐	☐	☐	☐	☐
6	☑	☐	US 2005006	2005032	35	Process for deposition of	438/478			Todd, Michael A. et	☐	☐	☐	☐	☐	☐
7	☑	☐	US 2005005	2005031	13	Semiconductor device wit	438/260			Steimle, Robert F. e	☐	☐	☐	☐	☐	☐
8	☑	☐	US 2005005	2005031	19	Organic electronic device	313/503	313/504;		Yu, Gang et al.	☐	☐	☐	☐	☐	☐

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